



JANTX2N6796U Information

Heisener.com

Part Number JANTX2N6796U

Manufacturer Microsemi Corporation

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 8A 18-BQFN Exposed Pad **Package**

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com For Reference Only E-mail: salesdept@heisener.com



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JANTX2N6796U Specifications

Manufacturer Part Number JANTX2N6796U Manufacturer Microsemi Corporation Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 18-BQFN Exposed Pad Series Military, MIL-PRF-19500/557 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 28.51nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 800mW (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 195 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 18-ULCC (9.14x7.49) Package / Case 18-BQFN Exposed Pad		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 18-BQFN Exposed Pad Series Military, MIL-PRF-19500/557 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 10put Capacitance (Ciss) (Max) @ Vds 28.5 In C @ 10V Input Capacitance (Ciss) (Max) @ Vds 220V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 195 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 18-BQFN Exposed Pad	Manufacturer Part Number	JANTX2N6796U
Package 18-BQFN Exposed Pad Series Military, MIL-PRF-19500/557 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 28.51nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 800mW (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 195 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 18-ULCC (9.14x7.49) Package / Case 18-BQFN Exposed Pad	Manufacturer	Microsemi Corporation
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SeriesMilitary, MIL-PRF-19500/557FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs28.5 ln C @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)800mW (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs195 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package18-ULCC (9.14x7.49)Package / Case18-BQFN Exposed Pad		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs28.51nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)800mW (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs195 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package18-ULCC (9.14x7.49)Package / Case18-BQFN Exposed Pad	Package	18-BQFN Exposed Pad
Technology Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 28.51nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 800mW (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 195 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 18-ULCC (9.14x7.49) Package / Case	Series	Military, MIL-PRF-19500/557
Drain to Source Voltage (Vdss)100 VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10 VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs28.51nC @ 10 VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20 VFET Feature-Power Dissipation (Max)800mW (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs195 mOhm @ 8A, 10 VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package18-ULCC (9.14x7.49)Package / Case18-BQFN Exposed Pad	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs28.51nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)800mW (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs195 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package18-ULCC (9.14x7.49)Package / Case18-BQFN Exposed Pad	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs28.51nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)800mW (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs195 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package18-ULCC (9.14x7.49)Package / Case18-BQFN Exposed Pad	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	8A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 18-ULCC (9.14x7.49) Package / Case 28.51nC @ 10V - 800mW (Ta), 25W (Tc) 195 mOhm @ 8A, 10V -55°C ~ 150°C (TJ) Surface Mount Supplier Device Package	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 800mW (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 195 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 18-ULCC (9.14x7.49) Package / Case 18-BQFN Exposed Pad	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)800mW (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs195 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package18-ULCC (9.14x7.49)Package / Case18-BQFN Exposed Pad	Gate Charge (Qg) (Max) @ Vgs	28.51nC @ 10V
FET Feature - Power Dissipation (Max) 800mW (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 195 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 18-ULCC (9.14x7.49) Package / Case 18-BQFN Exposed Pad	Input Capacitance (Ciss) (Max) @ Vds	-
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 195 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 18-ULCC (9.14x7.49) Package / Case 18-BQFN Exposed Pad	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs195 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package18-ULCC (9.14x7.49)Package / Case18-BQFN Exposed Pad	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 18-ULCC (9.14x7.49) Package / Case 18-BQFN Exposed Pad	Power Dissipation (Max)	800mW (Ta), 25W (Tc)
Mounting Type Surface Mount Supplier Device Package 18-ULCC (9.14x7.49) Package / Case 18-BQFN Exposed Pad	Rds On (Max) @ Id, Vgs	195 mOhm @ 8A, 10V
Supplier Device Package 18-ULCC (9.14x7.49) Package / Case 18-BQFN Exposed Pad	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 18-BQFN Exposed Pad	Mounting Type	Surface Mount
• • •	Supplier Device Package	18-ULCC (9.14x7.49)
Report errors?	Package / Case	18-BQFN Exposed Pad
		Report errors?

JANTX2N6796U Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

JANTX2N6796U Payment Methods



















JANTX2N6796U Shipping Methods













If you have any question about JANTX2N6796U, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com